



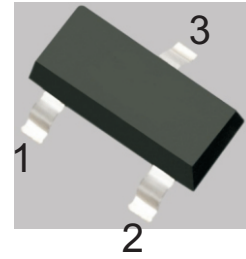
SS8050

NPN TRANSISTOR

FEATURES

- Complimentary to SS8550

SOT-23



1.BASE  
2.EMITTER  
3.COLLECTOR

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CB0}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current — Continuous	$I_C$	1.5	A
Collector Power Dissipation	$P_C$	300	mW
Thermal Resistance From Junction To Ambient	$R_{thJA}$	417	°C/W
Operation Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~+150	°C

CLASSIFICATION OF  $h_{FE1}$

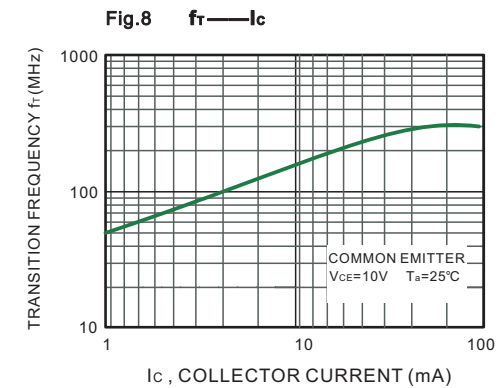
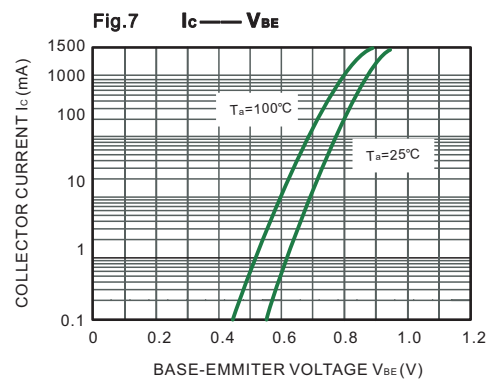
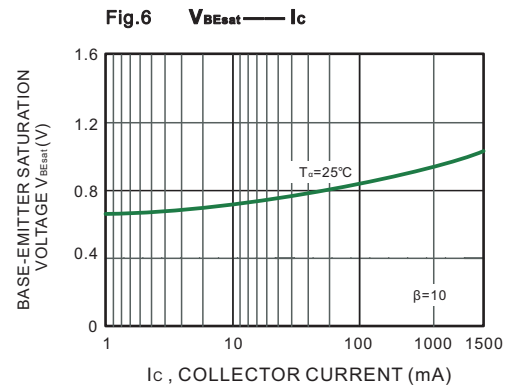
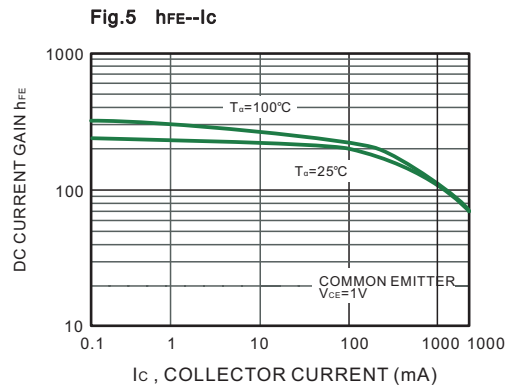
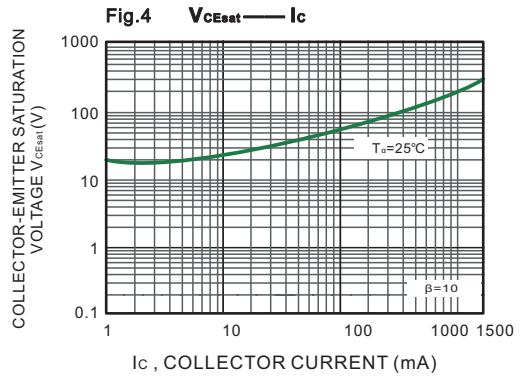
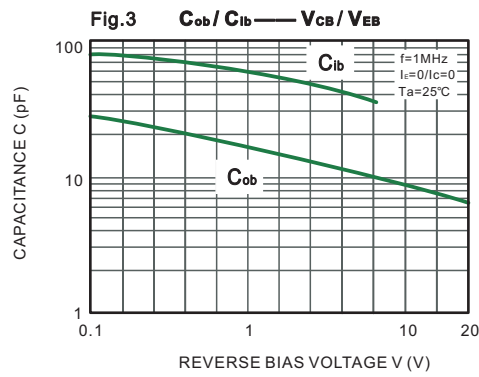
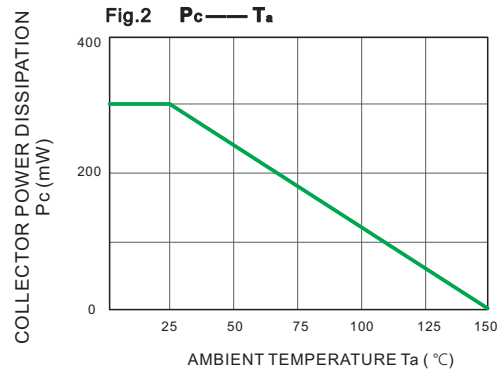
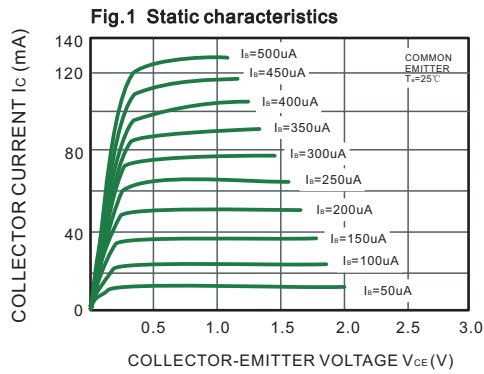
Rank	L	H	J
Range	120-200	200-350	300-400

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{ mA}, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 40V, I_E = 0$			0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = 20V, I_E = 0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$			0.1	$\mu A$
DC current gain	$h_{FE1}$	$V_{CE} = 1V, I_C = 100mA$	120		400	
	$h_{FE2}$	$V_{CE} = 1V, I_C = 800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800mA, I_B = 80mA$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800mA, I_B = 80mA$			1.2	V
Transition frequency	$f_T$	$V_{CE} = 10V, I_C = 50mA, f = 30MHz$	100			MHz

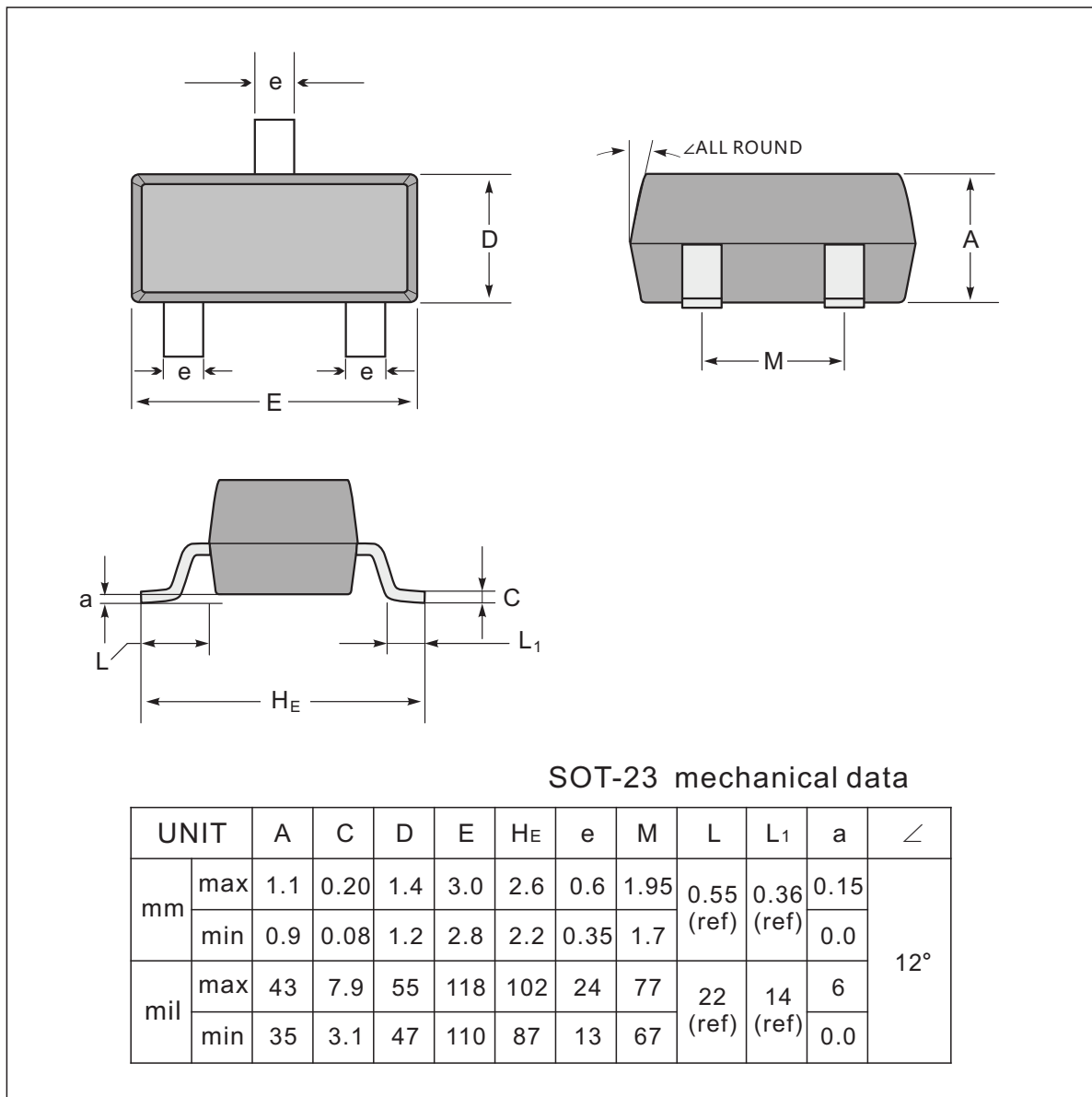


### TYPICAL CHARACTERISTICS

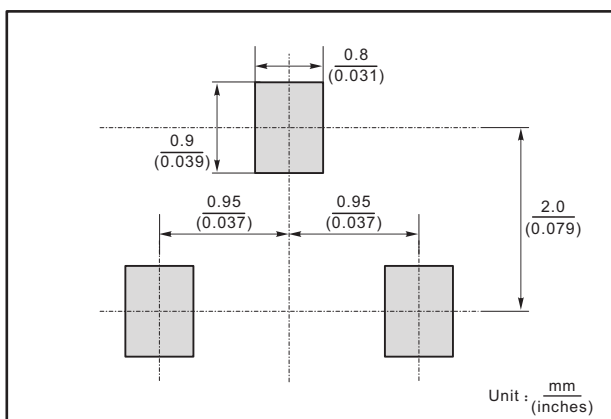




### SOT-23 Package Outline Dimensions



#### The recommended mounting pad size



#### Marking

Type number	Marking code
SS8050	Y1